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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/879,724	06/12/2001	Dong-Hyuk Ju	F0522	4898
7	7590 08/19/2003			
Renner, Otto,			EXAMINER	
Boisselle & Sklar, LLP			SEFER, AHMED N	
19th Floor				
1621 Euclid Avenue			ART UNIT	PAPER NUMBER
Cleveland, OH	44115-2191		2826	
			DATE MAILED: 08/19/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

			Il			
		Application No.	Applicant(s)			
		09/879,724	JU ET AL.			
Office Action Summary		Examiner	Art Unit			
		A. Sefer	2826			
-	The MAILING DATE of this communication appears on the cover sheet with the correspondence address					
Period for		ALC OFT TO EVOIDE 2 MONTH	(S) EDOM			
THE N - Exten after S - If the - If NO - Failur	DRTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. sions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period vertor to reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing of patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ti y within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS from	mely filed ys will be considered timely. n the mailing date of this communication. ED (35 U.S.C. § 133).			
1)🛛	Responsive to communication(s) filed on 191	<u>May 2003</u> .				
2a)⊠		is action is non-final.				
3)□	20/23 This detail is the merits is					
Disposition of Claims						
4)⊠	4)⊠ Claim(s) <u>1-3,5 and 17-27</u> is/are pending in the application.					
	4a) Of the above claim(s) is/are withdra	wn from consideration.				
•	•—					
6)⊠	S)⊠ Claim(s) <u>1-3,5 and 17-19</u> is/are rejected.					
	7) Claim(s) <u>20-27</u> is/are objected to.					
8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers						
9)☐ The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
441	The proposed drawing correction filed on	is: a) ☐ approved b) ☐ disapp	roved by the Examiner.			
11)[]	If approved, corrected drawings are required in re					
12) The oath or declaration is objected to by the Examiner.						
Priority under 35 U.S.C. §§ 119 and 120 13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) All b) Some * c) None of:						
a	The second secon					
	Certified copies of the priority documents have been received in Application No Certified copies of the priority documents have been received in Application No					
3. Copies of the certified copies of the priority documents have been received in this National Stage						
*	application from the International B See the attached detailed Office action for a lis	tof the certified copies not rece	ived.			
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
	 a) The translation of the foreign language p Acknowledgment is made of a claim for domest 	rovisional application has been r	eceived.			
Attachme						
1) Not	ice of References Cited (PTO-892) ice of Draftsperson's Patent Drawing Review (PTO-948) ormation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Inform	nary (PTO-413) Paper No(s) nal Patent Application (PTO-152)			

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DETAILED ACTION

Response to Amendment

1. The amendment filed on 5/19/03 has been entered; and new claims 20-27 have been added.

Specification

2. Claims 1 and 18 are objected to because of the following informalities: It is suggested that the limitation "wherein the LTCM layer comprises at least one of doped amorphous silicon, undoped amorphous silicon and undoped porous silicon, wherein when the LTCM layer is doped amorphous silicon a dopant species is selected from one of boron, phosphorous and fluorine" be rewritten to read "wherein the LTCM layer comprises at least one of doped amorphous silicon having a dopant species selected from one of boron, phosphorous and fluorine, undoped amorphous silicon and undoped porous silicon. Appropriate correction is required.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in-

⁽¹⁾ an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or

⁽²⁾ a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

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4. Claims 1-3, 5 are rejected under 35 U.S.C. 102(e) as being anticipated by Maeda USPN 6,285,072.

Maeda discloses in figs. 7-14 a semiconductor-on-insulator (SOI) structure having a semiconductor substrate 10 or silicon (as in claim 2); a leaky, thermally conductive insulator material (LTCIM) layer 11 disposed directly on the semiconductor substrate; and a semiconductor layer 15 disposed directly on the LTCIM layer having a thermal conductivity which falls within the range recited in the claim (as in claim 3) and resistivity value $10~\Omega$ -cm or greater (as in claim 5); and active regions defined in the semiconductor layer by isolation trenches 16 and the LTCM layer, wherein the LTCIM layer comprises undoped porous silicon, and wherein the LTCIM layer extends over an entire lateral dimension of the semiconductor substrate.

5. Claims 17-19 are rejected under 35 U.S.C. 102(e) as being anticipated by Maeda USPN 6,285,072.

Maeda discloses in figs. 7-14 a semiconductor-on-insulator (SOI) structure having a semiconductor substrate 10; a leaky, thermally conductive insulator material (LTCIM) layer 11 disposed directly on the semiconductor substrate; and a semiconductor layer 15 disposed directly on the LTCIM layer; wherein the LTCIM layer comprises undoped porous silicon, and wherein the LTCIM layer extends over an entire lateral dimension of the semiconductor substrate.

As to claims 17 and 19, Maeda discloses a gate defining a channel interposed between a source and a drain formed within an active region of the SOI structure (as in claim 19) and the active region defined in a semiconductor layer by isolation trenches 16 and an LTCM layer.

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Allowable Subject Matter

6. Claims 20-27 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

- 7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Iyer et al US PG-Pub No. 2002/0132395 disclose an SOI provided with an ion-implanted region, which may extend through a buried layer.
- 8. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to A. Sefer whose telephone number is (703) 605-1227.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601.

ANS July 31, 2003

> AMTHUM J. PLYNIN SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800